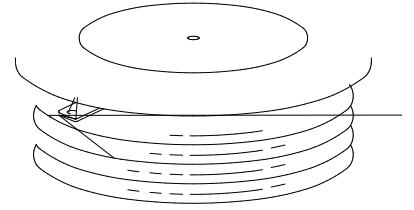

T11C



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP1400/46	4000	4000	4600
KP1400/48	4200	4200	4800
KP1400/50	4400	4400	5000
KP1400/52	4600	4600	5200

V_{RRM} = Repetitive peak reverse voltage
 V_{DRM} = Repetitive peak off state voltage
 V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 120 mA (3)
Critical rate of voltage rise	dv/dt (4)	2000 V/

Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		200		mA	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Gate- trigger voltage	V_{GT}	0.7	2.6		V	$V_D = 12\text{ V}; R_L = 3\text{ ohms}; T_j = +25\text{ }^\circ\text{C}$
Peak negative voltage	V_{GRM}		10		V	

Delay time	t_d			3.0	s	$I_{TM}=100A; V_D=67\%V_{DRM}$ $V_G=30V; R_G=10\text{ohms};$ $t_r=0.1\text{ s}; t_p=20\text{ s}$
Turn-off time (with $V_R = -5\text{ V}$)	t_q			600	s	$I_{TM} = 2000A; di/dt = -10A/ s;$ $V_R = 100V; dv/dt = 30V/ s;$ $V_D = 67\%V_{DRM}; T_j = 125$
Reverse recovery charge	Q_{rr}		2500		C	$I_{TM}=2000A\ di/dt=-10A/ s;$ $V_R=100V; T_j=125$

Operating temperature	T_j	-40	+125		$^\circ\text{C}$	
Storage temperature	T_{stg}	-40	+140		$^\circ\text{C}$	
Thermal resistance - junction to case	$R_{(j-c)}$		0.015		$^\circ\text{C/W}$	Double sided cooled
Thermal resistance - case to heatsink	$R_{(c-s)}$		0.004		$^\circ\text{C/W}$	Double sided cooled
Mounting force	F	32	36	34	kN	
Weight	m			1.0	kg	

* Mounting surfaces smooth, flat and greased

